

# T Kobayashi

## List of Publications by Year in descending order

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18  
papers

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times ranked

335  
citing authors

#	ARTICLE	IF	CITATIONS
1	Fixed-charge generation in SiO <sub>2</sub> /GaN MOS structures by forming gas annealing and its suppression by controlling Ga-oxide interlayer growth. Japanese Journal of Applied Physics, 2022, 61, SC1034.	0.8	9
2	Insight into interface electrical properties of metal-oxide-semiconductor structures fabricated on Mg-implanted GaN activated by ultra-high-pressure annealing. Applied Physics Letters, 2022, 120, .	1.5	11
3	Impact of nitridation on the reliability of 4H-SiC(112̄,0) MOS devices. Applied Physics Express, 2022, 15, 041002.	1.1	6
4	Short-Channel Effects in SiC MOSFETs Based on Analyses of Saturation Drain Current. IEEE Transactions on Electron Devices, 2021, 68, 1382-1384.	1.6	17
5	Physics and Innovative Technologies in SiC Power Devices. , 2021, , .		5
6	Effect of quantum confinement on the defect-induced localized levels in 4H-SiC(0001)/SiO <sub>2</sub> systems. Journal of Applied Physics, 2020, 128, .	1.1	13
7	Carbon dangling-bond center (carbon <i>P</i> center) at 4H-SiC(0001)/SiO <sub>2</sub> interface. Applied Physics Letters, 2020, 116, .	1.5	20
8	Design and formation of SiC (0001)/SiO <sub>2</sub> interfaces via Si deposition followed by low-temperature oxidation and high-temperature nitridation. Applied Physics Express, 2020, 13, 091003.	1.1	38
9	Formation of high-quality SiC(0001)/SiO <sub>2</sub> structures by excluding oxidation process with H <sub>2</sub> etching before SiO <sub>2</sub> deposition and high-temperature N <sub>2</sub> annealing. Applied Physics Express, 2020, 13, 121002.	1.1	25
10	Energetics and electronic structure of native point defects in $\alpha$ -Ga <sub>2</sub> O <sub>3</sub> . Applied Physics Express, 2019, 12, 091001.	1.1	35
11	Influence of vacuum annealing on interface properties of SiC (0001) MOS structures. Japanese Journal of Applied Physics, 2019, 58, 078001.	0.8	2
12	Structure and energetics of carbon defects in SiC (0001)/SiO <sub>2</sub> systems at realistic temperatures: Defects in SiC, SiO <sub>2</sub> , and at their interface. Journal of Applied Physics, 2019, 126, .	1.1	44
13	Native point defects and carbon clusters in 4H-SiC: A hybrid functional study. Journal of Applied Physics, 2019, 125, .	1.1	55
14	Reduction of interface state density in SiC (0001) MOS structures by low-oxygen-partial-pressure annealing. Applied Physics Express, 2019, 12, 031001.	1.1	15
15	Structural determination of phosphosilicate glass based on first-principles molecular dynamics calculation. Japanese Journal of Applied Physics, 2019, 58, 011001.	0.8	1
16	Estimation of Threshold Voltage in SiC Short-Channel MOSFETs. IEEE Transactions on Electron Devices, 2018, 65, 3077-3080.	1.6	28
17	Carbon ejection from a SiO <sub>2</sub> /SiC(0001) interface by annealing in high-purity Ar. Applied Physics Letters, 2017, 111, .	1.5	33
18	Progress and future challenges of SiC power devices and process technology. , 2017, , .		12